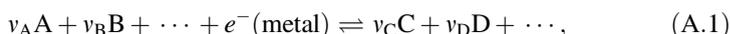


Appendix A

Derivation of the Nernst equation

Consider the general reaction [1, 2]



where v_i are the stoichiometric coefficients of the individual components i . With the *electrochemical potential* $\tilde{\mu}_i$ of component i being related to its chemical potential μ_i by

$$\tilde{\mu}_i = \mu_i + z_i F \phi, \quad (\text{A.2})$$

where $z_i F \phi$ is the electrical energy of species i (z_i is the charge carried by i , F is Faraday's constant, and ϕ is the potential of the particular phase (electrode or solution) in which i resides), the electrochemical potentials of the reactants and products in the equilibrium described by Eq. (A.1) can be expressed as

$$v_A \tilde{\mu}_A + v_B \tilde{\mu}_B + \dots + \tilde{\mu}_{e^-} = v_C \tilde{\mu}_C + v_D \tilde{\mu}_D + \dots \quad (\text{A.3})$$

The different $\tilde{\mu}_i$ can be substituted according to Eq. (A.2):

$$\begin{aligned} v_A (\mu_A + z_A F \phi_s) + v_B (\mu_B + z_B F \phi_s) + \dots + (\mu_{e^-} - F \phi_m) \\ = v_C (\mu_C + z_C F \phi_s) + v_D (\mu_D + z_D F \phi_s) + \dots \end{aligned} \quad (\text{A.4})$$

Conservation of electrical charge requires that

$$v_A z_A + v_B z_B + \dots - 1 = v_C z_C + v_D z_D + \dots \quad (\text{A.5})$$

Rearrangement of Eq. (A.4), substitution into Eq. (A.5), and solving for $F(\phi_m - \phi_s)$ leads to

$$F(\phi_m - \phi_s) = v_A \mu_A + v_B \mu_B + \cdots + \mu_{e^-} - v_C \mu_C - v_D \mu_D. \quad (\text{A.6})$$

With

$$\mu_i = \mu_i^0 + RT \ln a_i. \quad (\text{A.7})$$

follows

$$F(\phi_m - \phi_s) = v_A(\mu_A^0 + RT \ln a_A) + v_B(\mu_B^0 + RT \ln a_B) + \cdots + \mu_{e^-} - v_C(\mu_C^0 + RT \ln a_C) - v_D(\mu_D^0 + RT \ln a_D). \quad (\text{A.8})$$

Substitution of the term

$$F\Delta\phi^0 = (v_A \mu_A^0 + v_B \mu_B^0 + \cdots) - (v_C \mu_C^0 + v_D \mu_D^0 + \cdots) + \mu_{e^-}, \quad (\text{A.9})$$

which is constant at a fixed temperature and pressure, into Eq. (A.8), and rearrangement lead to a general statement of the Nernst equation:

$$\phi_m - \phi_s = \Delta\phi^0 + \frac{RT}{F} \ln \left\{ \frac{a_A^{v_A} a_B^{v_B} \cdots}{a_C^{v_C} a_D^{v_D} \cdots} \right\}. \quad (\text{A.10})$$

For ‘ideally’ behaving solutions activities can be approximated to concentrations. With $E = \phi_m - \phi_s$ and $E^0 = \Delta\phi^0$, and by introducing z for the number of electrons transferred in the process (as a means of generalisation to account for processes with $z > 1$), Eq. (A.9) can be rewritten as

$$E = E^0 + \frac{RT}{zF} \ln \frac{[\text{Ox}]}{[\text{Red}]}, \quad (\text{A.11})$$

which, when at equilibrium ($E = E_{\text{eq}}$), equates Eq. (2.7) in Sect. 2.2.4.

With the change in free energy ΔG being defined as the sum of the products of the stoichiometric coefficients v_i and the chemical potentials μ_i of the individual components i

$$\Delta G = \sum v_i \mu_i, \quad (\text{A.12})$$

the relationship between the Nernst equation and ΔG becomes apparent:

$$\Delta G = \sum v_i \mu_i^0 + RT \sum v_i \ln a_i \quad (\text{A.13})$$

or, rearranged:

$$\Delta G = \Delta G^0 + RT \ln \prod_i [a_i]^{v_i}. \quad (\text{A.14})$$

Hence,

$$\Delta G = -zFE. \quad (\text{A.15})$$

Appendix B

Derivation of the Mott-Schottky Equation

Consider an n -type semiconductor under depletion [3]. The density of electrons and holes at the surface, n_s and p_s , respectively, is related to their constant bulk values by

$$n(x) = n_b e^{\frac{e_0 \Delta \phi}{k_B T}} \quad \text{and} \quad p(x) = p_b e^{-\frac{e_0 \Delta \phi}{k_B T}}, \quad (\text{B.1})$$

where $\Delta \phi = \phi_x - \phi_b$ represents the surface-bulk potential difference, i.e. the band-bending, and n_b and p_b are the electron and hole concentrations in the bulk of the semiconductor. The potential, the charge density (ρ), and the number of carriers (n and p) all depend on the distance (x) away from the interface into the semiconductor bulk. The charge density in an n -type semiconductor can be expressed as [4]

$$\rho(x) = e_0(-n(x) + p(x) - N_A + N_D) \quad (\text{B.2})$$

and $n \gg p$, $N_D \gg N_A$. Further, the density of electrons in the bulk principally equals the donor density, i.e. $n_b \approx N_D$. Using these simplifications, Eq. (B.2) can be rewritten as follows:

$$\rho(x) = e_0 N_D \left(1 - e^{\frac{e_0 \Delta \phi}{k_B T}} \right). \quad (\text{B.3})$$

The charge density is related to the potential by the Poisson equation [5]:

$$\frac{d^2 \phi(x)}{dx^2} = \frac{-\rho(x)}{\epsilon_r \epsilon_0}. \quad (\text{B.4})$$

Using the substitution

$$v = -\Delta\phi = -(\phi_x - \phi_b) \quad (\text{B.5})$$

Equation (B.4) can be expressed as

$$-\frac{d^2v}{dx^2} = -\frac{\rho(x)}{\varepsilon_r\varepsilon_0} \quad (\text{B.6})$$

and substituted in Eq. (B.3):

$$\frac{d^2v}{dx^2} = \frac{e_0N_D}{\varepsilon_r\varepsilon_0} \left(1 - e^{\frac{-e_0v}{k_B T}}\right). \quad (\text{B.7})$$

With the property of derivatives [5]

$$\frac{d^2v}{dx^2} = \frac{1}{2} \frac{d}{dv} \left(\frac{dv}{dx}\right)^2 \quad (\text{B.8})$$

Equation (B.7) transforms into

$$d\left(\frac{dv}{dx}\right)^2 = \frac{2e_0N_D}{\varepsilon_r\varepsilon_0} \left(1 - e^{\frac{-e_0v}{k_B T}}\right) dv. \quad (\text{B.9})$$

Integration gives

$$\left(\frac{dv}{dx}\right)^2 = \frac{2e_0N_D}{\varepsilon_r\varepsilon_0} \left(v + \frac{k_B T}{e_0} e^{\frac{-e_0v}{k_B T}}\right) + \text{const.} \quad (\text{B.10})$$

Taking into account that in the bulk of the semiconductor ($x \rightarrow \infty$) $\phi_x = \phi_b$, i.e. there is no potential difference between two points ($v = 0$) and $\frac{dv}{dx} = 0$,

$$\left(\frac{dv}{dx}\right)^2 = \frac{2e_0N_D}{\varepsilon_r\varepsilon_0} \left(v - \frac{k_B T}{e_0} \left(1 - e^{\frac{-e_0v}{k_B T}}\right)\right). \quad (\text{B.11})$$

At the surface with $x = 0$; $v = v_s$, the following approximation can be used for the depletion layer of the semiconductor:

$$v_s \gg \frac{k_B T}{e_0}. \quad (\text{B.12})$$

Then, Eq. (B.11) simplifies to

$$\left(\frac{dv}{dx}\right)_{x=0} = \left(\frac{2e_0N_D}{\varepsilon_r\varepsilon_0}\left(v_s - \frac{k_B T}{e_0}\right)\right)^{1/2}. \quad (\text{B.13})$$

Using Gauss' law to express the total charge Q [4] as

$$Q = \varepsilon_r\varepsilon_0\left(\frac{dv}{dx}\right), \quad (\text{B.14})$$

and combining Eqs. (B.13) and (B.14), Eq. (B.15) is obtained:

$$Q = \left(2\varepsilon_r\varepsilon_0e_0N_D\left(v_s - \frac{k_B T}{e_0}\right)\right)^{1/2}. \quad (\text{B.15})$$

The interfacial capacitance of the space-charge layer C_{sc} is given as

$$C_{sc} = \frac{dQ}{dv_s}. \quad (\text{B.16})$$

Substitution of Eq. (B.15) into Eq. (B.16) and differentiation yields

$$C_{sc} = \frac{\varepsilon_r\varepsilon_0e_0N_D}{\sqrt{2}\sqrt{\varepsilon_r\varepsilon_0e_0N_D\left(v_s - \frac{k_B T}{e_0}\right)}} = \left(\frac{2}{\varepsilon_r\varepsilon_0e_0N_D}\left(v_s - \frac{k_B T}{e_0}\right)\right)^{-1/2}. \quad (\text{B.17})$$

With $v_s = 0$ at $E = E_{fb}$

$$v_s = E - E_{fb}, \quad (\text{B.18})$$

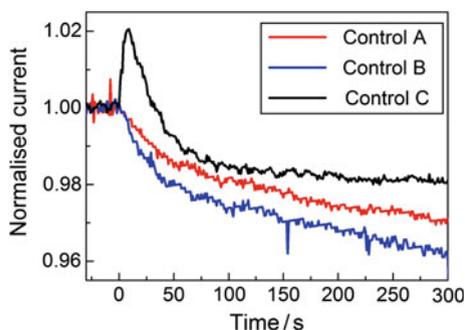
and Eq. (B.17) transforms into the Mott-Schottky equation Eq. (2.40) [3]:

$$C_{sc}^{-2} = \frac{2}{\varepsilon_r\varepsilon_0e_0N_D}\left(E - E_{fb} - \frac{k_B T}{e_0}\right). \quad (\text{B.19})$$

Appendix C

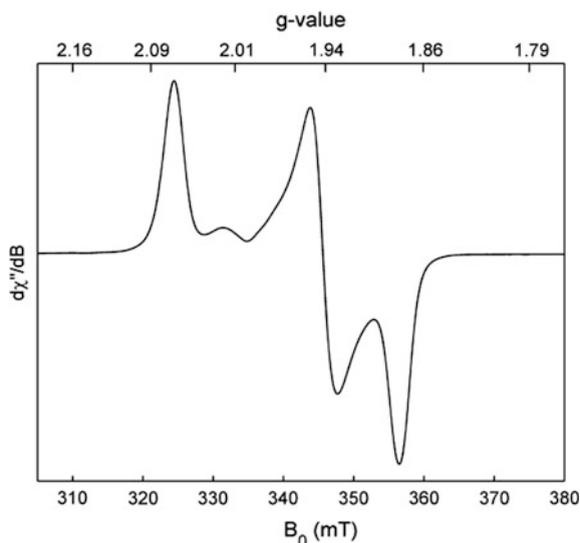
The Effect of H₂ Consumption by CaHydA at High Potential

The effect of H₂ consumption by *CaHydA* at oxidising potentials was determined by chronoamperometry, since in inhibition studies using acetaldehyde (described in Sect. 3.2.3) the gas flow had to be interrupted simultaneously to aldehyde injection, because of the high volatility of MeCHO (bp 20 °C). The figure below depicts three control experiments carried out analogously to the inhibition studies described in Sect. 3.2.3, apart from buffer solution being injected into the electrochemical cell at $t = 0$ instead of acetaldehyde (H₂ flow was turned off simultaneously to buffer injection; the electrode was poised at 0.0 V vs. SHE; $\omega = 3000$ rpm; pH 6.0 phosphate buffer; dark). In all three cases, less than 5% activity is lost during 5 min, the typical time-course of an actual inhibition experiment.



Appendix D

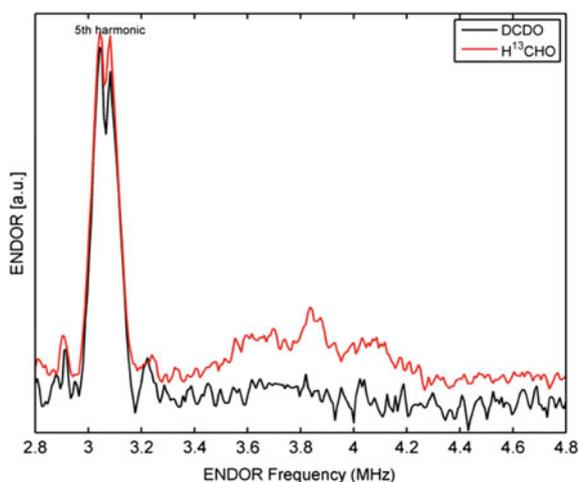
Continuous-Wave EPR Spectrum of Formaldehyde-Inhibited CrHydA1



X-band EPR spectrum of formaldehyde-inhibited *CrHydA1* collected at 11 K, 9.3902 GHz, with a total spin concentration of 830 μM . Non-saturating conditions were employed, i.e. microwave power of 1 mW, modulation amplitude of 1 Gauss, and digital smoothing of 10 points of 1 point per Gauss in a sweep of 1500 G in 10 s. The minor signal at 330 mT ($g = 2.025$) most likely corresponds to a decay product following HCHO inhibition of *CrHydA1*.

Appendix E

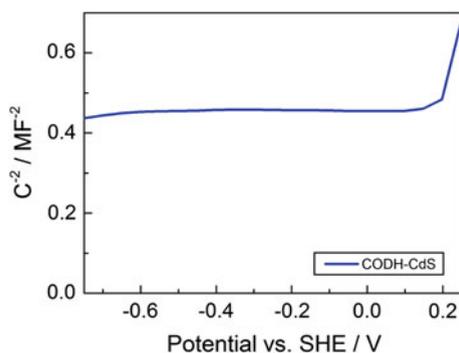
X-Band ENDOR Natural Abundance Carbon Control



X-band ENDOR spectrum of a ²H control, DCDO, with natural abundance carbon (i.e. approximately 99% ¹²C), compared to formaldehyde isotopically labelled with ¹³C. The two spectra are scaled to the 5th harmonic of the ¹H-ENDOR signal (as indicated in the figure). Data was collected at $g = 1.944$, under the same conditions as in Fig. 3.18. Reprinted with permission from [6]. Copyright 2016 American Chemical Society

Appendix F

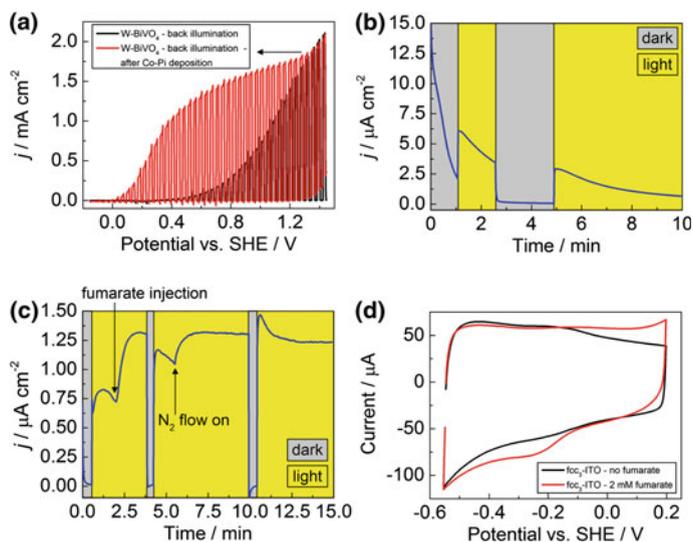
Mott-Schottky Experiment on CODH-CdS



Mott-Schottky plot ($1/C^2$ vs. E) recorded at 20 °C, 1 kHz for CODH-CdS under 100% N_2 in a 0.2 M MES (pH 6.0) cell buffer solution.

Appendix G

Photoelectrocatalytic Fumarate Reduction Under Inverse Connections



Photoelectrocatalysis experiment carried out with reversed connections, i.e. Co-Pi-W-BiVO₄ as the working electrode and fcc₃-ITO as counter. (a) Linear sweep voltammograms recorded before and after Co-Pi deposition on W-BiVO₄; 10 mV s⁻¹, chopped illumination (0.5 Hz, back illumination), 25 °C, 0.1 M KPi buffer (pH 7.0). (b) Current vs. time trace of the Co-Pi-W-BiVO₄ WE connected to the bare *meso*-ITO electrode (CE) in a two-compartment photoelectrochemical cell at zero external bias. Conditions: no gas flow, 25 °C, 0.1 M KPi buffer (pH 7.0). (c) Chronoamperometry experiment depicting photocurrent densities corresponding to visible-light-driven fumarate reduction; 25 °C, 0.1 M KPi buffer (pH 7.0). The

reduction compartment was sparged with N_2 to allow efficient substrate transport to the electrode, gas flow was turned off during injection of fumarate (final concentration 2 mM) into the reduction compartment at $t = 2.0$ min. (d) Cyclic voltammogram of fcc_3 -ITO recorded after chronoamperometry experiments depicted in (c); 30 mV s^{-1} , $25 \text{ }^\circ\text{C}$, 0.1 M KPi buffer (pH 7.0), N_2 flow. The red trace, recorded after introducing fumarate (final concentration 2 mM) into the solution, shows that the enzyme is still catalytically active towards fumarate reduction.

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